SP010N08GTQ

100V N-Channel Power MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	8.5mΩ@10V	65A
	11mΩ@4.5V	

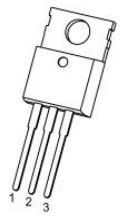
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

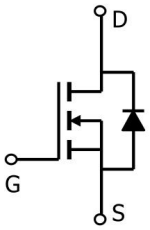
- Power switching application
- PWM Application
- DC-DC Converter

Package

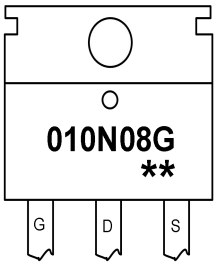


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



010N08G =Device Code
** =Week Code

Order Information

Device	Package	Unite/Tube
SP010N08GTQ	TO-220-3L	50

Absolute maximum ratings (Ta=25℃ unless otherwise noted)

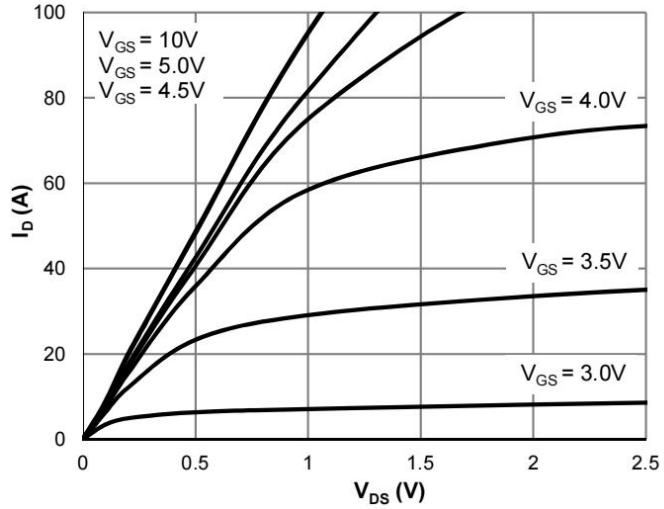
Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current(Tc=25℃)	I_D	65	A
Pulsed Drain Current[2]	I_{DM}	260	A
Single Pulse Avalanche Energy [3]	E_{AS}	156	mJ
Total Power Dissipation [4](Tc=25℃)	P_D	90	W
Thermal Resistance Junction-Case [1]	$R_{\theta JC}$	1.38	℃/W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃

Electrical characteristics (Ta=25℃, unless otherwise noted)

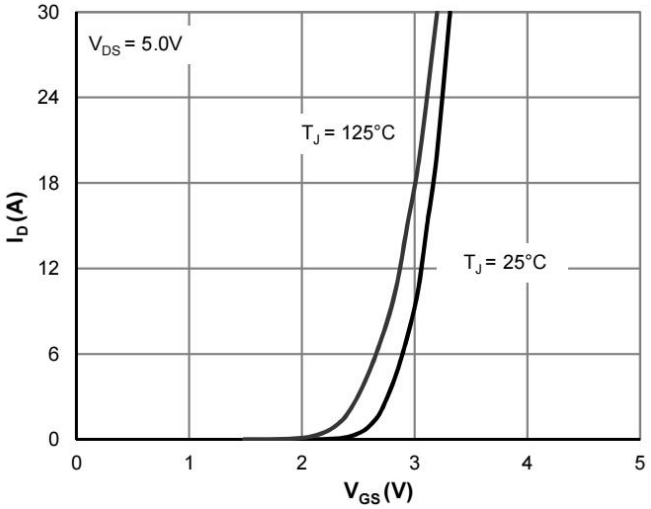
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	VGS=0V , ID=250uA	100	---	---	V
Drain-Source Leakage Current	I_{DSS}	VDS=80V , VGS=0V , TJ=25℃	---	---	1	uA
Gate-Source Leakage Current	I_{GSS}	VGS=±20V , VDS=0V	---	---	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	VGS=VDS , ID =250uA	1.2	1.9	2.5	V
Static Drain-Source On-Resistance[2]	$R_{DS(ON)}$	VGS=10V , ID=20A	---	8.5	12	mΩ
		VGS=4.5V , ID=15A	---	11	15	
Dynamic Characteristics						
Input Capacitance	C_{iss}	VDS=50V , VGS=0V , f=1MHz	---	1635	---	pF
Output Capacitance	C_{oss}		---	339	---	
Reverse Transfer Capacitance	C_{rss}		---	22	---	
Switching Characteristics						
Total Gate Charge (4.5V)	Q_g	VDS=50V , VGS=10V , ID=20A	---	14	---	nC
Gate-Source Charge	Q_{gs}		---	5	---	
Gate-Drain Charge	Q_{gd}		---	7	---	
Turn-On Delay Time	$T_{d(on)}$	VDD=50V, VGS=10V , R_L=2.5Ω , R_G=6Ω	---	8	---	ns
Rise Time	T_r		---	16	---	
Turn-Off Delay Time	$T_{d(off)}$		---	31	---	
Fall Time	T_f		---	27	---	
Source-Drain Diode Characteristics						
Diode Forward Voltage[2]	V_{SD}	VGS=0V , IS=1A , TJ=25℃	---	---	1.2	V

Note :
1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3. The EAS data shows Max. rating . The test condition is VDD=50V,VGS=10V,L=0.5mH,Rg=25Ω
4. The power dissipation is limited by 150℃ junction temperature

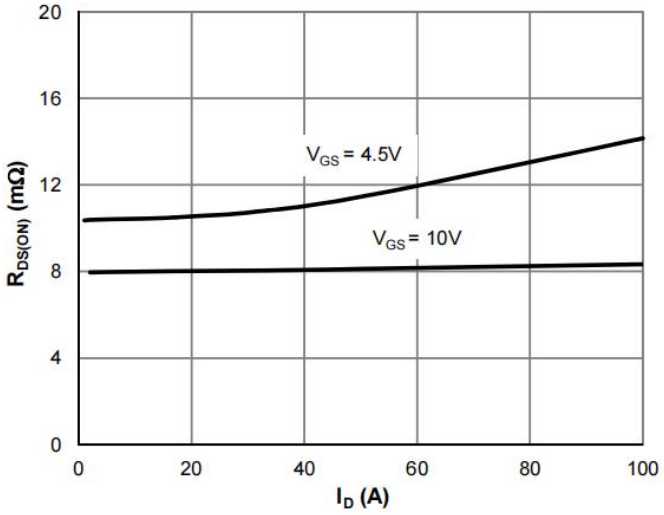
Typical Characteristics



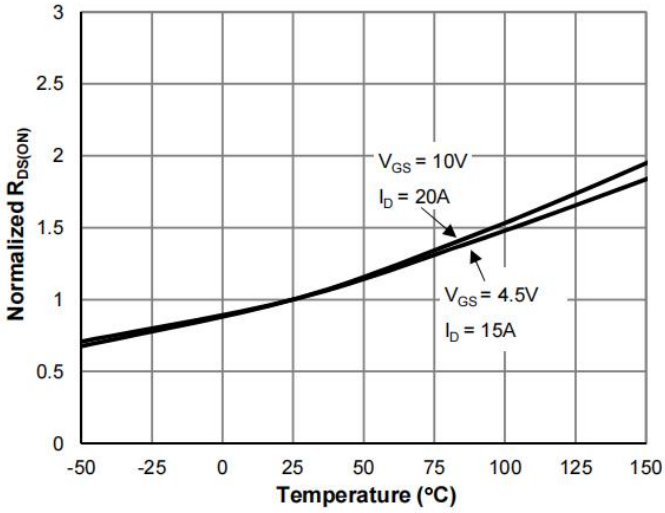
Typical Output Characteristics



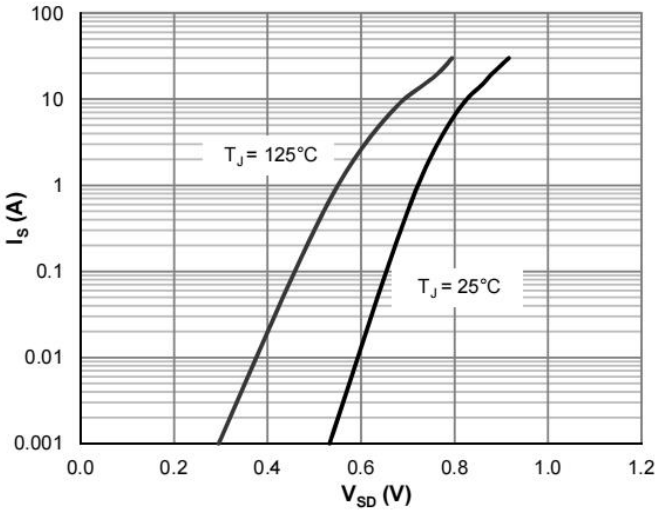
Transfer Characteristics



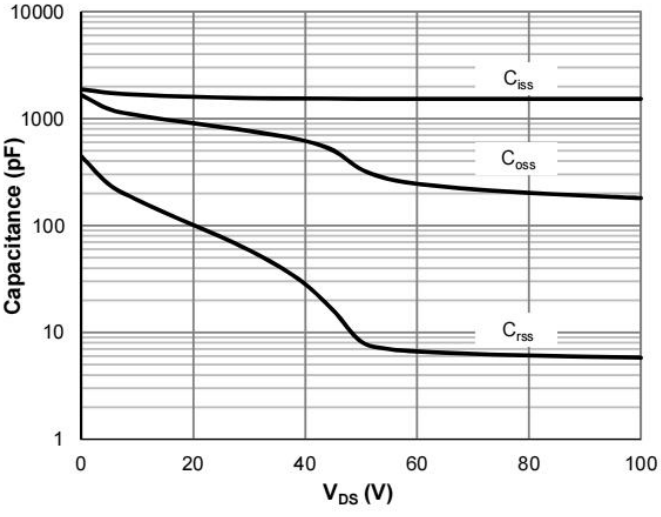
On-Resistance vs.Drain Current



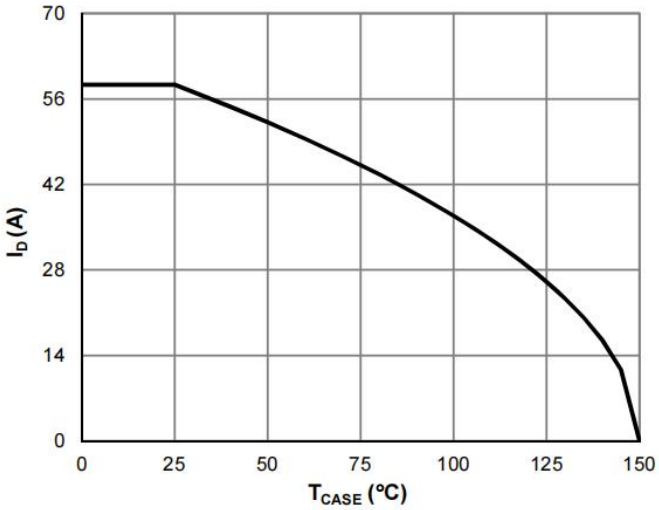
On-Resistance vs.Junction Temperature



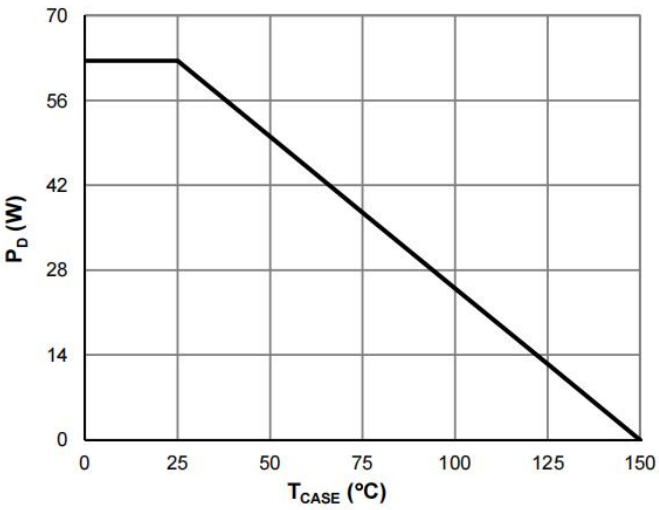
Body-Diode Characteristics



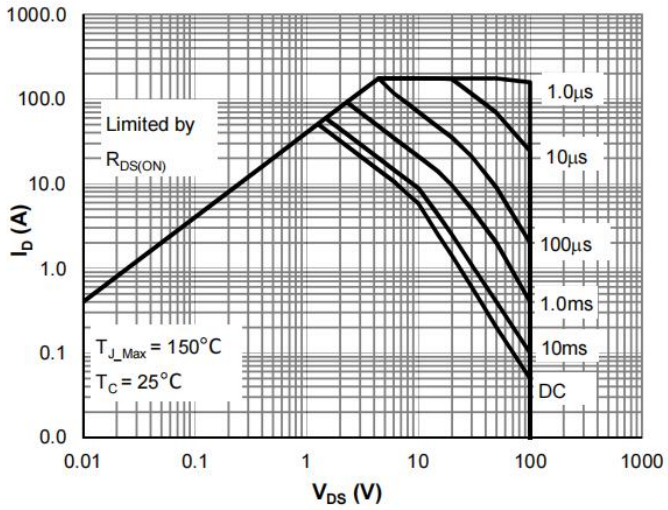
Capacitance Characteristics



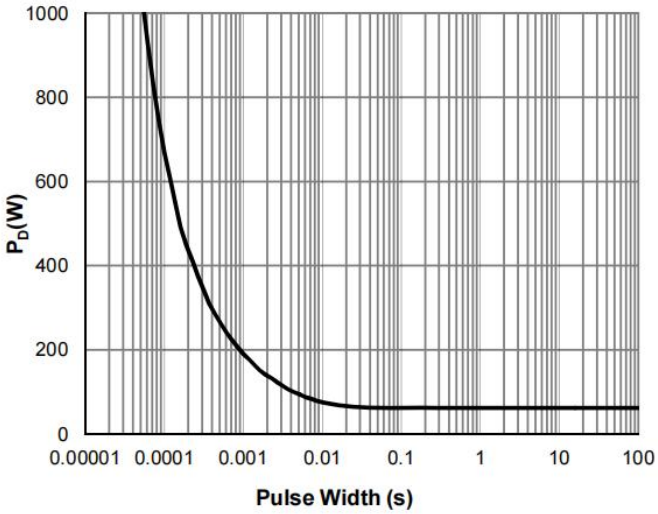
Current De-rating



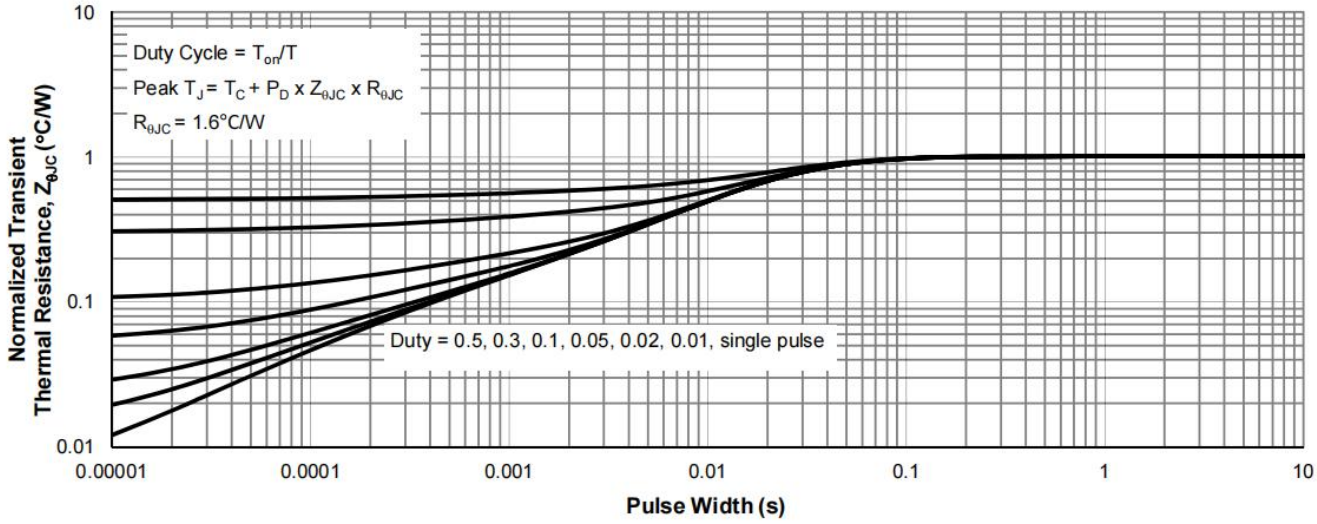
Power De-rating



Maximum Safe Operating Area

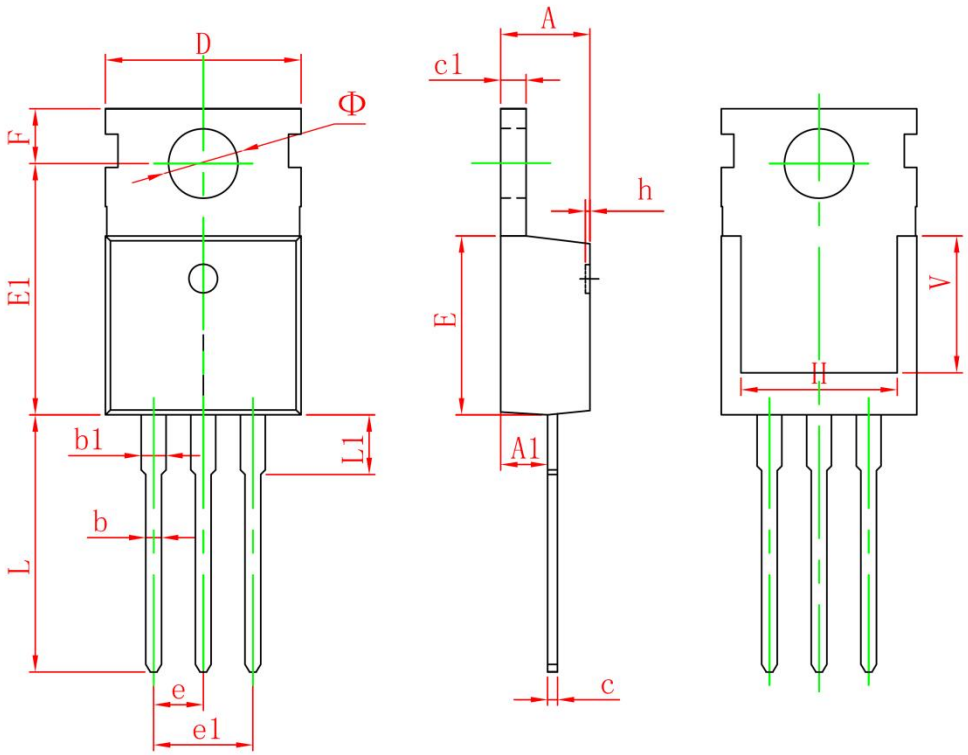


Single Pulse Power Rating,Junction-to-Case



Normalized Maximum Transient Thermal Impedance

TO-220-3L-C Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150